

Device Modeling Report

COMPONENTS:
DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD
PART NUMBER: RHRG50120
MANUFACTURER: INTERSIL
REMARK:TC=110 C

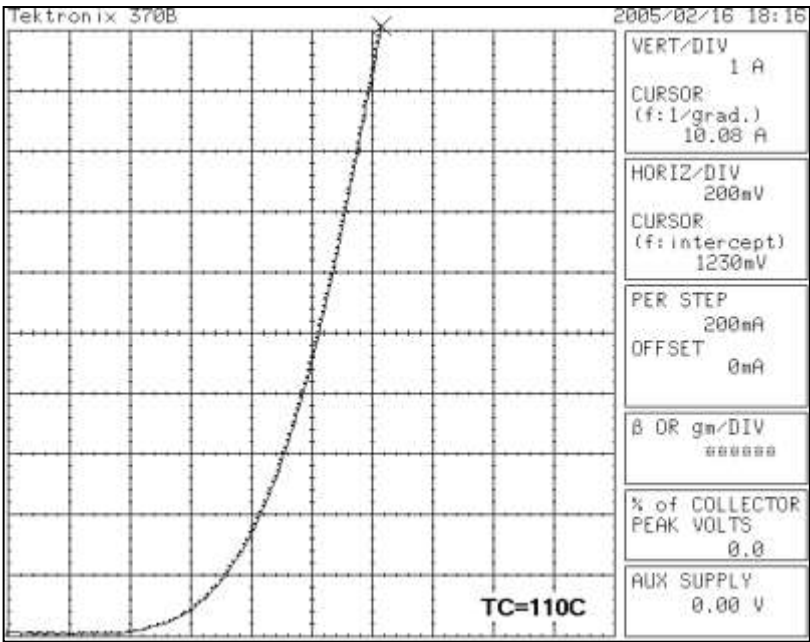


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

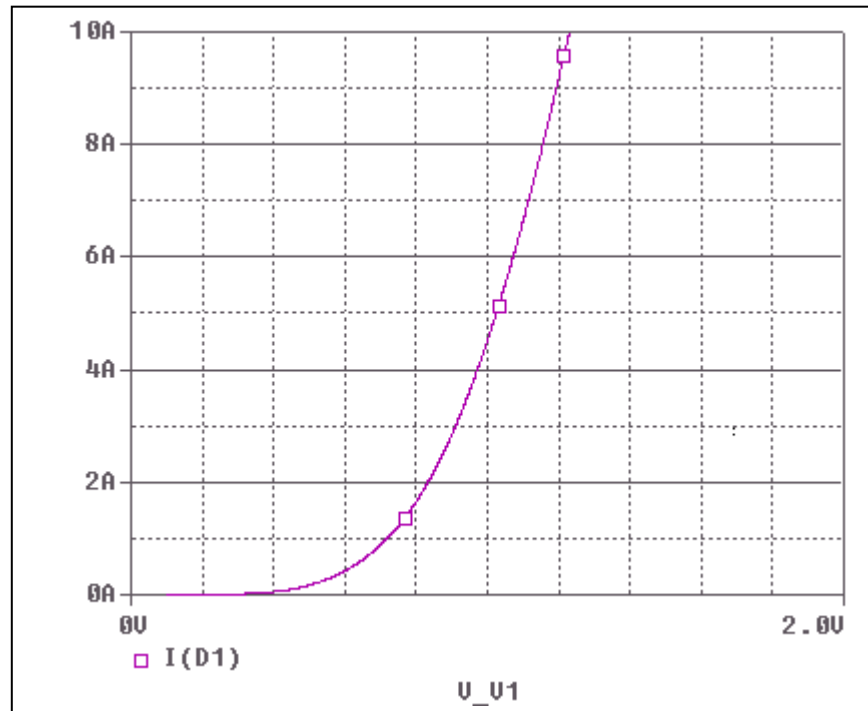
Forward Current Characteristic

Reference

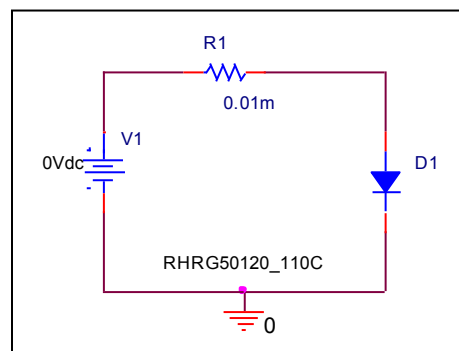


Forward Current Characteristic

Circuit Simulation Result

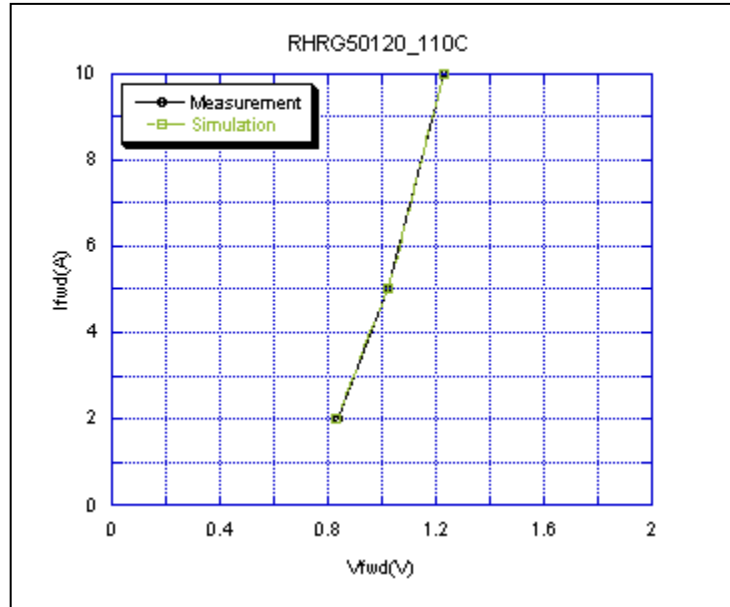


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

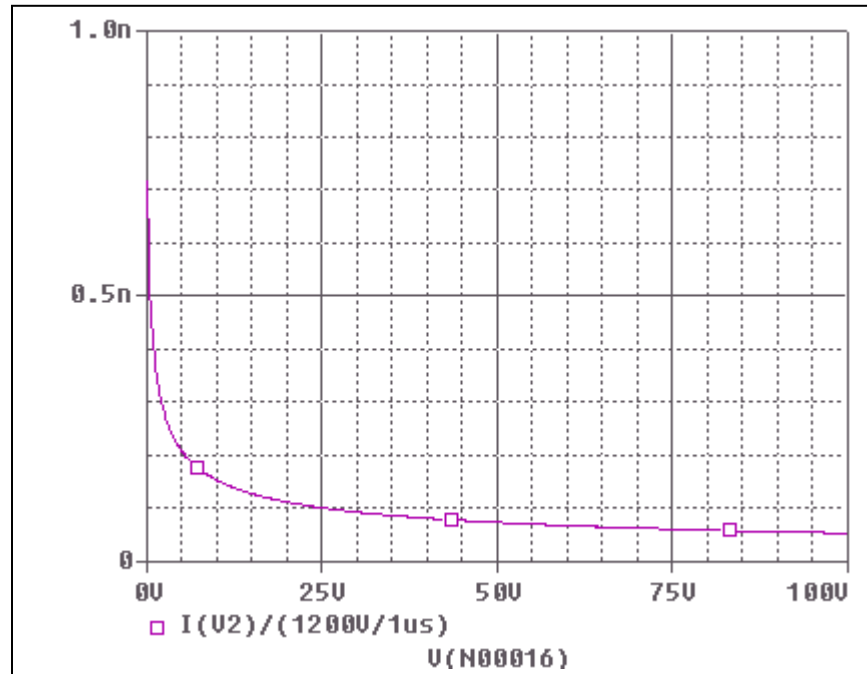


Simulation Result

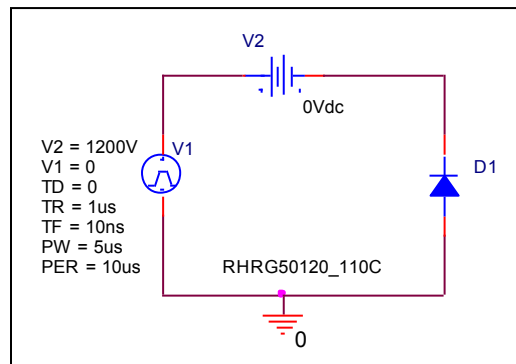
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
1	0.718	0.718	0.00
2	0.834	0.832	0.24
5	1.024	1.024	0.00
10	1.230	1.229	0.08

Capacitance Characteristic

Circuit Simulation Result

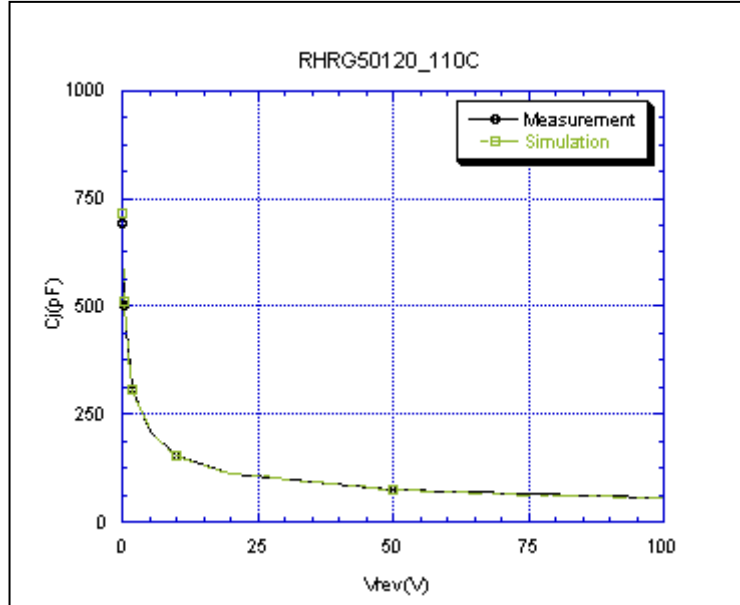


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

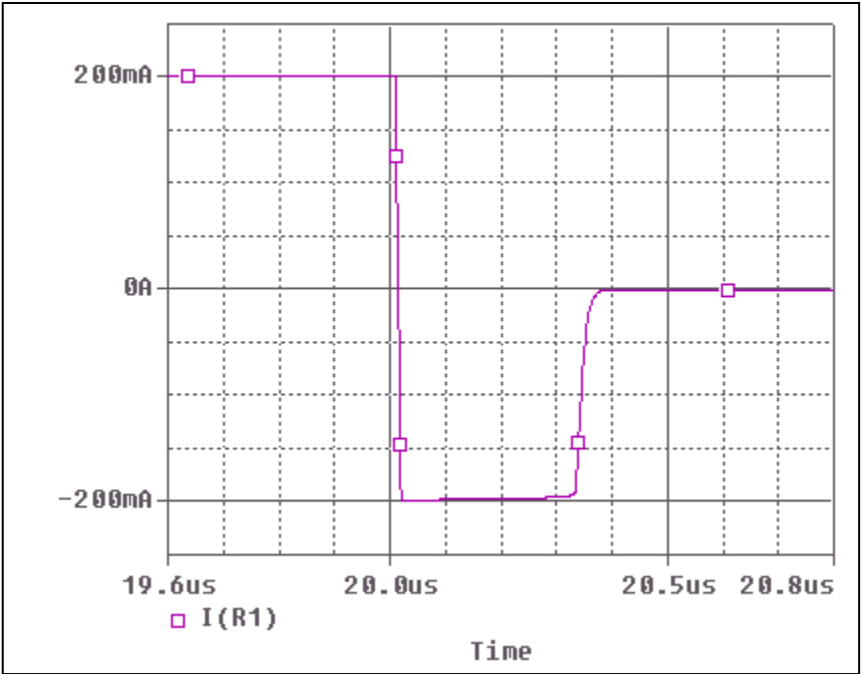


Simulation Result

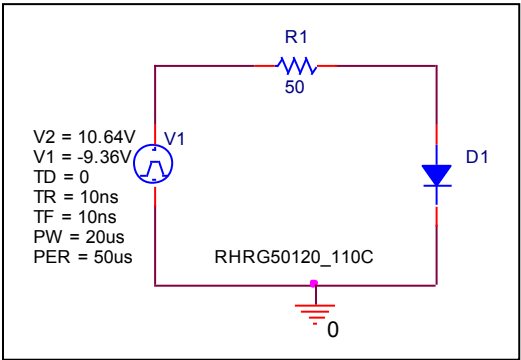
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	781.778	781.778	0.00
0.1	690.695	715.812	-3.64
0.2	613.016	634.910	-3.57
0.5	499.991	510.211	-2.04
1	399.767	403.830	-1.02
2	309.406	308.602	0.26
5	209.334	209.200	0.06
10	153.530	153.801	-0.18
20	111.860	112.603	-0.66
50	73.206	74.081	-1.19
100	53.061	53.820	-1.43

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

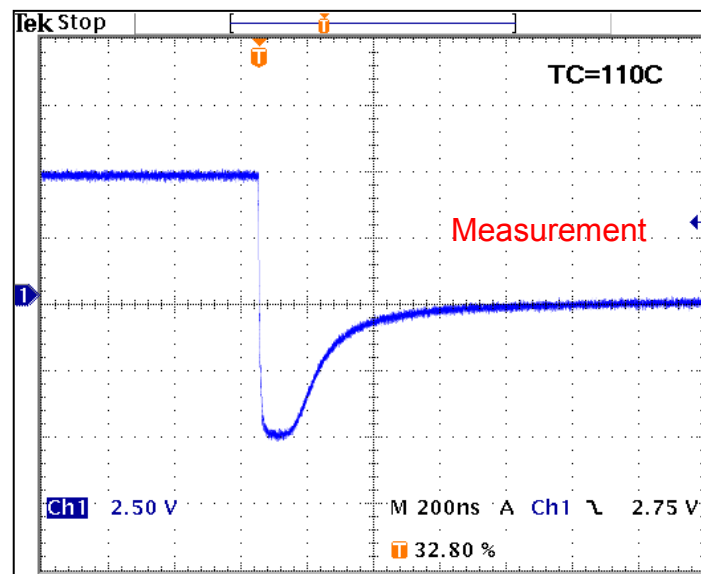


Compare Measurement vs. Simulation

trr	Measurement		Simulation		%Error
	344.00	ns	343.92	ns	0.022

Reverse Recovery Characteristic

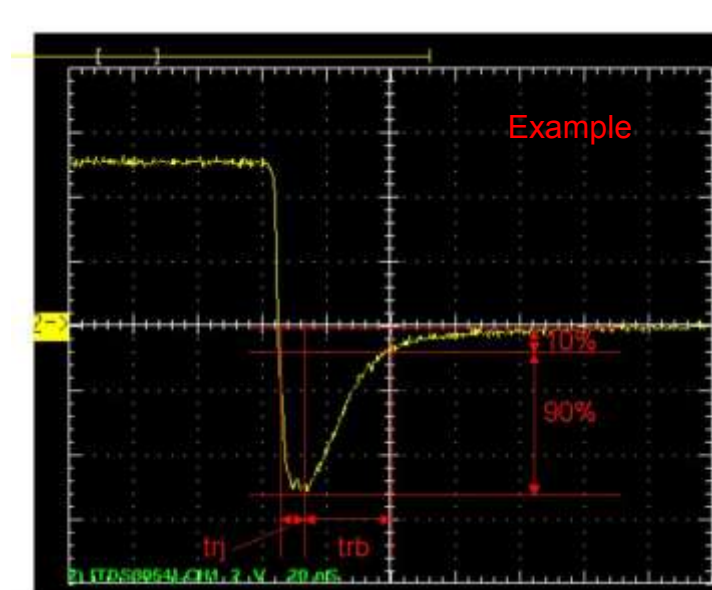
Reference



$T_{rj} = 88(\text{ns})$

$T_{rb} = 256(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.2(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}